

OCT 10 2006

Docket No.: 503.38097CX1

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-8. (Canceled)

9. (New) A semiconductor device comprising:

a semiconductor substrate;

a first electrode provided on a front plane of said semiconductor substrate, said first electrode containing an Al layer as a main component;

a second electrode provided on a rear plane of said semiconductor substrate;

a first metallic member disposed over said first electrode, said first metallic member being electrically connected to said first electrode;

a second metallic member disposed under said second electrode, said second metallic member being electrically connected to said second electrode; and

wherein a plurality of Au bumps are disposed between said first electrode and said first metallic member,

wherein said first electrode, said Au bumps and said first metallic member are electrically connected,

wherein said first metallic member is plated with a precious metal film, and

wherein said front plane of said semiconductor substrate and each of said Au bumps are connected via an Au Al alloy layer.

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10. (New) A semiconductor device according to claim 9,  
wherein said semiconductor substrate and parts of said first and second  
metallic members are covered by a resin body, and  
wherein a bottom face of said second metallic member is exposed from  
said resin body.

11. (New) A semiconductor device according to claim 9,  
wherein said first metallic member is comprised of a first portion and a  
second portion, said first portion is positioned over said first electrode and said  
second portion extends in direction from said first electrode to second electrode, and  
a bottom face of said second portion and a bottom face of said second metallic  
member are at a substantially same level.

12. (New) A semiconductor device according to claim 9,  
wherein said semiconductor device is a surface mounting type device.

13. (New) A semiconductor device according to claim 9,  
wherein said precious metal film contains Pd.

14. (New) A semiconductor device according to claim 9,  
wherein each of said first and second metallic members contains a Cu  
core.

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15. (New) A semiconductor device according to claim 9,  
wherein said second electrode and second metallic member are  
connected via a Ag paste.

16. (New) A semiconductor device according to claim 9,  
wherein said semiconductor substrate includes a MOSFET,  
wherein said first electrode is electrically connected to a source region of  
said MOSFET, and  
wherein said second electrode is electrically connected to a drain region  
of said MOSFET.

17. (New) A semiconductor device according to claim 9,  
wherein said semiconductor substrate is made of Si.

18. (New) A semiconductor device according to claim 9,  
wherein said semiconductor substrate and parts of said first and second  
metallic members are covered by a resin body,  
wherein a bottom face of said second metallic member is exposed from  
said resin body, and  
wherein said first metallic member is comprised of a first portion and a  
second portion, said first portion is positioned over said first electrode and said  
second portion extends in a direction from said first electrode to second electrode,  
and a bottom face of said second portion and a bottom face of said second metallic  
member are at a substantially same level.

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19. (New) A semiconductor device according to claim 18,  
wherein said semiconductor device is a surface mounting device.
20. (New) A semiconductor device according to claim 18,  
wherein said precious metal film contains Pd.
21. (New) A semiconductor device according to claim 18,  
wherein each of said first and second metallic members contains a Cu  
core.
22. (New) A semiconductor device according to claim 18,  
wherein said second electrode and second metallic member are  
connected via a Ag paste.
23. (New) A semiconductor device according to claim 18,  
wherein said semiconductor substrate includes a MOSFET,  
wherein said first electrode is electrically connected to a source region of  
said MOSFET, and  
wherein said second electrode is electrically connected to a drain region  
of said MOSFET.
24. (New) A semiconductor device according to claim 18,  
wherein said semiconductor substrate is made of Si.